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**HALOGEN** 

FREE GREEN

(5-2008)



### Vishay Semiconductors

## Infrared Emitting Diode, 950 nm, GaAs



TSUS6402 is an infrared, 950 nm emitting diode in GaAs

technology molded in a blue-gray tinted plastic package.

#### **FEATURES**

Package type: leadedPackage form: T-1¾

• Dimensions (in mm): Ø 5

• Peak wavelength:  $\lambda_p = 950 \text{ nm}$ 

High reliability

• Angle of half intensity:  $\varphi = \pm 22^{\circ}$ 

Low forward voltage

· Suitable for high pulse current operation

· Good spectral matching with Si photodetectors

 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>



- Infrared remote control and free air transmission systems with low forward voltage and small package requirements
- Emitter in transmissive sensors
- · Emitter in reflective sensors

PRODUCT SUMMARY				
COMPONENT	I <sub>e</sub> (mW/sr)	φ (deg)	λ <sub>p</sub> (nm)	t <sub>r</sub> (ns)
TSUS6402	30	± 22	950	800

#### Note

**DESCRIPTION** 

• Test conditions see table "Basic Characteristics"

ORDERING INFORMATI	ON		
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSUS6402	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾

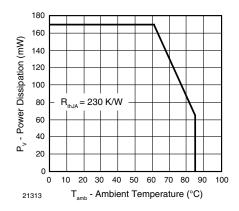
#### Note

• MOQ: minimum order quantity

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V <sub>R</sub>	5	V	
Forward current		l <sub>F</sub>	150	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I <sub>FM</sub>	300	mA	
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	2.5	А	
Power dissipation		$P_V$	170	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T <sub>amb</sub>	-40 to +85	°C	
Storage temperature range		T <sub>stg</sub>	-40 to +100	°C	
Soldering temperature	$t \le 5$ s, 2 mm from case	T <sub>sd</sub>	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R <sub>thJA</sub>	230	K/W	



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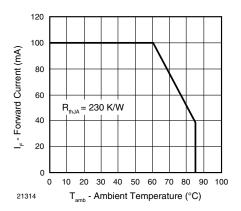


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T <sub>amb</sub> = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V <sub>F</sub>		1.3	1.7	V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 100 mA	TK <sub>VF</sub>		- 1.3		mV/K
Reverse current	$V_R = 5 V$	I <sub>R</sub>			100	μA
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz, E = 0	Cj		30		pF
Dedicat intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	I <sub>e</sub>	15	30	50	mW/sr
Radiant intensity	$I_F = 1.5 \text{ A}, t_p = 100 \ \mu\text{s}$	I <sub>e</sub>	120	190 15 - 0.8 ± 22	mW/sr	
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фe		15		mW
Temperature coefficient of $\phi_e$	I <sub>F</sub> = 20 mA	TKφ <sub>e</sub>		- 0.8		%/K
Angle of half intensity		φ		± 22		deg
Peak wavelength	I <sub>F</sub> = 100 mA	$\lambda_{p}$		950		nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ		50		nm
Temperature coefficient of λ <sub>p</sub>	I <sub>F</sub> = 100 mA	TKλ <sub>p</sub>		0.2		nm/K
Rise time	I <sub>F</sub> = 100 mA	t <sub>r</sub>		800		ns
Rise time	I <sub>F</sub> = 1.5 A	t <sub>r</sub>		400		ns
E-II time	I <sub>F</sub> = 100 mA	t <sub>f</sub>		800		ns
Fall time	I <sub>F</sub> = 1.5 A	t <sub>f</sub>		400		ns
Virtual source diameter		d		2.9		mm
Forward voltage	$I_F = 1.5 \text{ A}, t_p = 100 \mu\text{s}$	V <sub>F</sub>		2.2	2.7	V

## Vishay Semiconductors

### BASIC CHARACTERISTICS (T<sub>amb</sub> = 25 °C, unless otherwise specified)

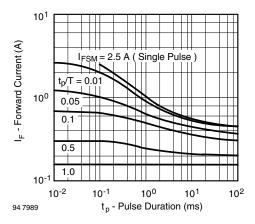


Fig. 3 - Pulse Forward Current vs. Pulse Duration

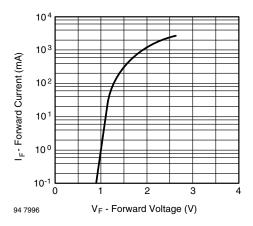


Fig. 4 - Forward Current vs. Forward Voltage

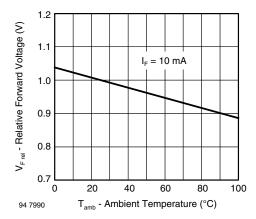


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

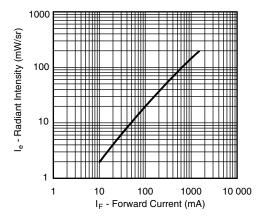


Fig. 6 - Radiant Intensity vs. Forward Current

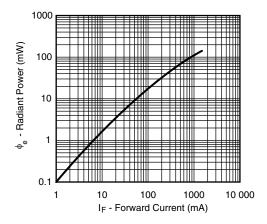


Fig. 7 - Radiant Power vs. Forward Current

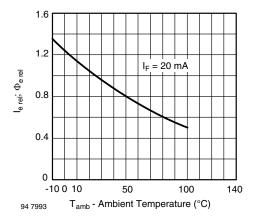


Fig. 8 - Relative Radiant Intensity / Power vs. Ambient Temperature



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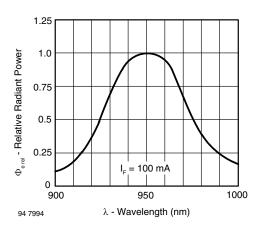


Fig. 9 - Relative Radiant Power vs. Wavelength

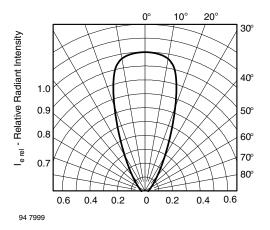
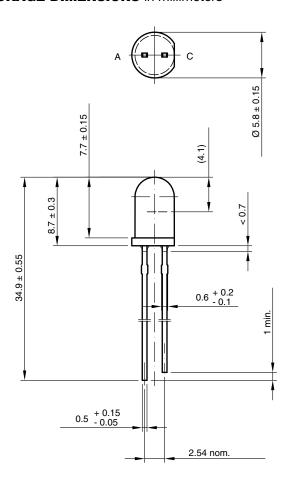
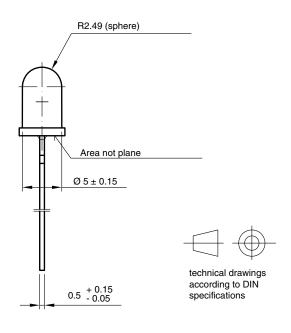


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

### **PACKAGE DIMENSIONS** in millimeters



6.544-5259.08-4 Issue: 3; 19.05.09





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